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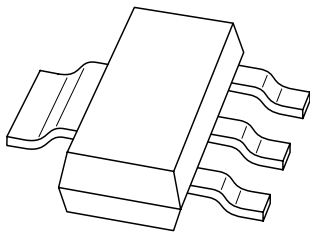
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Kind regards,

Team Nexperia

DATA SHEET



PZTA14 NPN Darlington transistor

Product data sheet
Supersedes data of 1997 Sep 04

1999 Apr 14

NPN Darlington transistor

PZTA14

FEATURES

- High current (max. 500 mA)
- Low voltage (max. 30 V).

APPLICATIONS

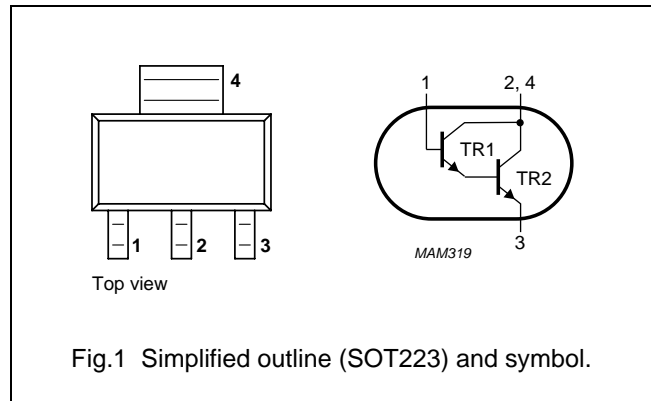
- Pre-amplifiers requiring high input impedance.

DESCRIPTION

NPN Darlington transistor in a SOT223 plastic package.
PNP complement: PZTA64.

PINNING

PIN	DESCRIPTION
1	base/input
2, 4	collector/output
3	emitter/ground



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	30	V
V_{CES}	collector-emitter voltage	$V_{BE} = 0$	–	30	V
V_{EBO}	emitter-base voltage	open collector	–	10	V
I_C	collector current (DC)		–	500	mA
I_{CM}	peak collector current		–	800	mA
I_B	base current (DC)		–	200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$; note 1	–	1.25	W
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C

Note

1. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm². For other mounting conditions, see “Thermal considerations for SOT223 in the General Part of associated Handbook”.

NPN Darlington transistor

PZTA14

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	100	K/W
$R_{th\ j-s}$	thermal resistance from junction to soldering point		19	K/W

Note

1. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm². For other mounting conditions, see "Thermal considerations for SOT223 in the General Part of associated Handbook".

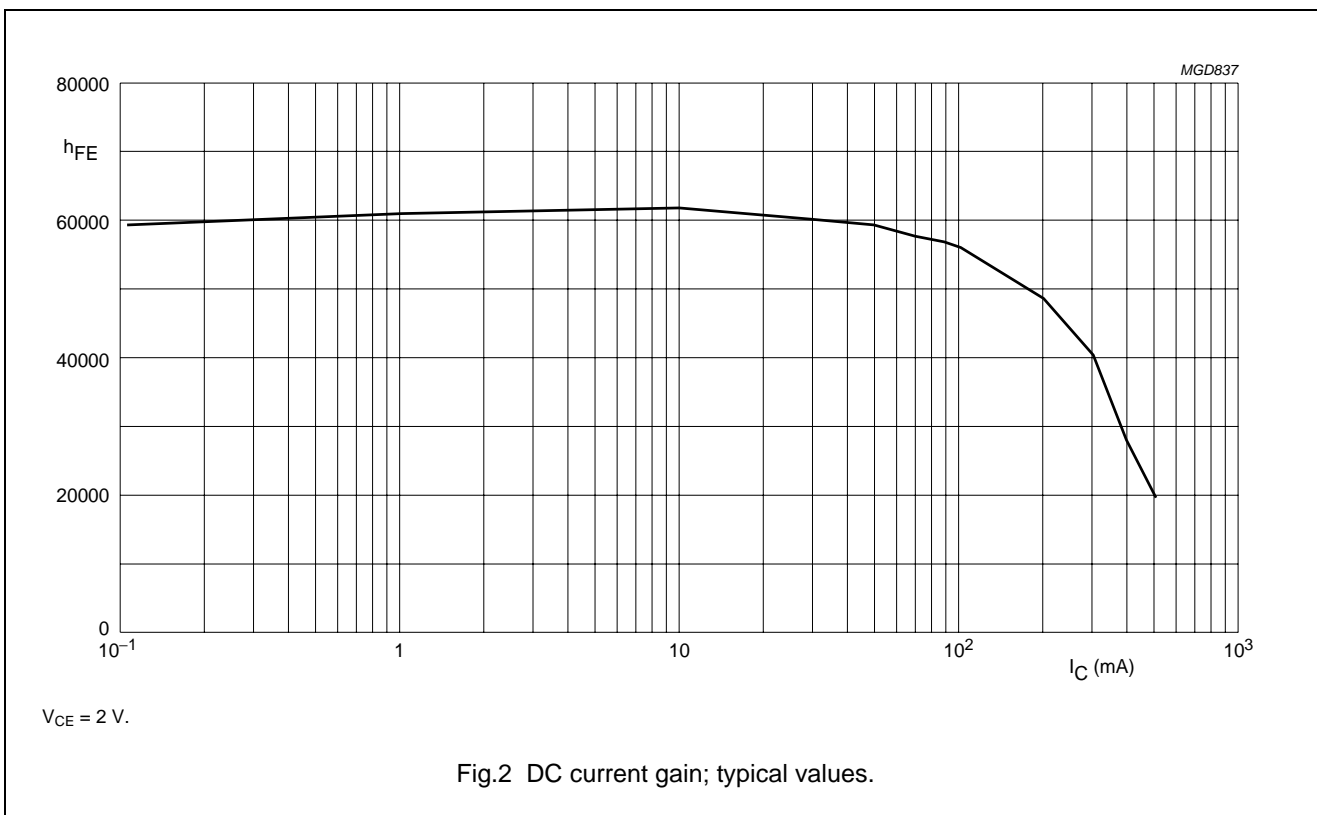
CHARACTERISTICS

$T_j = 25\text{ }^\circ\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = 30\text{ V}$	–	100	nA
I_{CES}	collector cut-off current	$V_{BE} = 0; V_{CE} = 30\text{ V}$	–	100	nA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = 10\text{ V}$	–	100	nA
h_{FE}	DC current gain	$V_{CE} = 5\text{ V}$; (see Fig.2) $I_C = 10\text{ mA}$ $I_C = 100\text{ mA}$	10000 20000	– –	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 100\text{ mA}; I_B = 0.1\text{ mA}$	–	1.5	V
V_{BEon}	base-emitter on-state voltage	$I_C = 100\text{ mA}; V_{CE} = 5\text{ V}$	–	2	V
f_T	transition frequency	$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}; f = 100\text{ MHz}$	125	–	MHz

NPN Darlington transistor

PZTA14



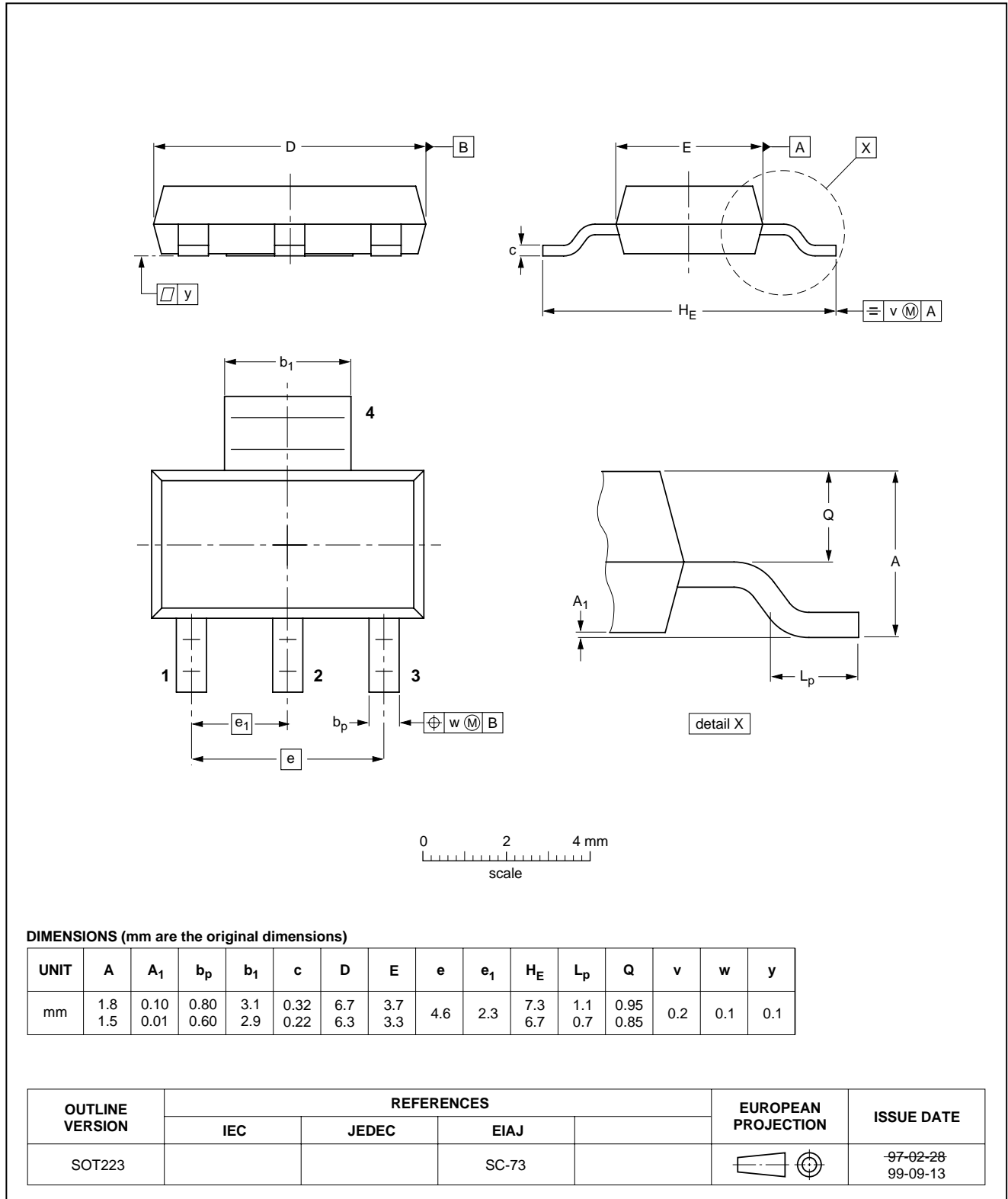
NPN Darlington transistor

PZTA14

PACKAGE OUTLINE

Plastic surface mounted package; collector pad for good heat transfer; 4 leads

SOT223



NPN Darlington transistor

PZTA14

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

1. Please consult the most recently issued document before initiating or completing a design.
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